Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An electro-optical device comprising, above a substrate:

a data ~~lines~~ line extending in a first direction;

a scanning ~~lines~~ line extending in a second direction and intersecting the data ~~lines;~~ line;

a pixel ~~electrodes~~ electrode and a thin film ~~transistors~~ transistor disposed so as to correspond to an intersection ~~regions~~ region of the data ~~lines~~ line and the scanning ~~lines;~~line;

a storage ~~capacitors~~ capacitor electrically connected to the thin film ~~transistors~~ transistor and the pixel ~~electrodes;~~ electrode; and

a shielding ~~layers~~ layer disposed between the data ~~lines~~ line and the pixel ~~electrodes,~~electrode,

a nitride ~~films~~ film being included in the shielding ~~layers~~ layer and ~~are~~ being formed along the data ~~lines~~ line and ~~being~~ wider than the data ~~lines.~~ line.

2. (Currently Amended) The electro-optical device according to Claim 1, a planarization process being performed on ~~the surfaces~~ a surface of an interlayer insulating ~~films~~ film arranged as ~~the bases~~ a base of the pixel ~~electrodes.~~ electrode.

3. (Currently Amended) The electro-optical device according to Claim 1, ~~each of~~ the data ~~lines~~ line being formed of the same film as one of a pair of electrodes which constitute ~~each of the~~ a storage ~~capacitors.~~ capacitor.

4. (Currently Amended) The electro-optical device according to Claim 3, the data ~~lines~~ line forming a laminated structure of an aluminum film and a conductive polysilicon film.

5. (Currently Amended) The electro-optical device according to Claim 1, further comprising:

a relay ~~layers~~ layer being electrically connected to the pixel ~~electrodes~~ electrode and one of a pair of electrodes which constitute ~~each of the~~ a storage ~~capacitors.~~ capacitor.

6. (Currently Amended) The electro-optical device according to Claim 5, the relay ~~layers~~ layer being made of an aluminum ~~films~~ film and a nitride ~~films.~~ film.

7. (Currently Amended) The electro-optical device according to Claim 5, the shielding ~~layers~~ layer being formed of the same ~~films~~ film as the relay ~~layers.~~ layer.

8. (Currently Amended) The electro-optical device according to Claim 1, the nitride ~~films~~ film being formed on ~~the surfaces~~ a surface of the data ~~lines.~~ line.

9. (Withdrawn-Currently Amended) An electro-optical device comprising, above a substrate:

a data ~~lines~~ line extending in a first direction;

a scanning ~~lines~~ line extending in a second direction and intersecting the data ~~lines;~~ line;

a pixel ~~electrodes~~ electrode and a thin film ~~transistors~~ transistor disposed so as to correspond to an intersection ~~regions~~ region of the data ~~lines~~ line and the scanning ~~lines;~~ line;

a storage ~~capacitors~~ capacitor electrically connected to the thin film ~~transistors~~ transistor and the pixel ~~electrodes;~~ electrode; and

a shielding ~~layers~~ layer disposed between the data ~~lines~~ line and the pixel ~~electrodes,~~electrode,

a nitride ~~films~~ film being included in the data ~~lines.~~line.

10. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the nitride ~~films~~ film being formed in ~~regions~~ a region where the scanning ~~lines extend.~~ line extends.

11. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the nitride ~~films~~ film being formed around an image display ~~regions~~ region defined as ~~regions~~ a region where the pixel ~~electrodes,~~ electrode, the data ~~lines,~~ line and the scanning ~~lines~~ line are formed.

12. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the nitride ~~films~~ film formed on the data ~~lines~~ line being wider than the data ~~lines.~~ line.

13. (Withdrawn-Currently Amended) The electro-optical device according to Claim 12, each ~~of the edges~~ edge of the nitride ~~films~~ film being larger than each ~~of the edges~~ edge of the data ~~lines~~ line by 0.1 to 2.2 μm.

14. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the thickness of the nitride ~~films~~ film being 10 to 100 nm.

15. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, further comprising:

another substrate that faces the substrate with an electro-optical material interposed therebetween and a light-shielding ~~films~~ film formed on the other substrate so as to correspond to the scanning ~~lines~~ line and the data ~~lines,~~ line,

the nitride ~~films~~ film being narrower than the light-shielding ~~films.~~ film.

16. (Withdrawn-Currently Amended) The electro-optical device according to Claim 15, each ~~of the edges~~ edge of the nitride ~~films~~ film being smaller than each ~~of the edges~~ edge of the light-shielding ~~films~~ film by up to 1 μm.

17. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, further comprising:

another substrate that faces the substrate with an electro-optical material interposed therebetween and a light-shielding ~~films~~ film formed on the other substrate so as to correspond to the scanning ~~lines~~ line and the data ~~lines,~~ line,

the nitride ~~films~~ film being wider than the light-shielding ~~films.~~ film.

18. (Currently Amended) The electro-optical device according to Claim 1, the shielding ~~layers~~ layer being formed of a transparent conductive material and ~~are~~ being formed over ~~the~~ an entire surface of the substrate.

19. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the shielding ~~layers~~ layer being formed of a transparent conductive material and being formed over the entire surface of the substrate in a mat shape.

20. (Withdrawn-Currently Amended) An electro-optical device comprising, above a substrate:

a data ~~lines~~ line extending in a first direction;

a scanning ~~lines~~ line extending in a second direction and intersecting the data ~~lines;~~ line;

a pixel ~~electrodes~~ electrode and a thin film ~~transistors~~ transistor disposed so as to correspond to an intersection ~~regions~~ region of the data ~~lines~~ line and the scanning ~~lines;~~ line;

a storage ~~capacitors~~ capacitor electrically connected to the thin film ~~transistors~~ transistor and the pixel ~~electrodes;~~ electrode; and

a shielding ~~layers~~ layer disposed between the data ~~lines~~ line and the pixel ~~electrodes,~~ electrode,

a dielectric ~~films~~ film which ~~constitute~~ constitutes the storage ~~capacitors~~ capacitor being made of a plurality of layers including different materials and one of the plurality of the layers being made of a material having a higher dielectric constant than those of the other layers, and

a nitride ~~films~~ film being included in the data ~~lines.~~ line.

21. (Currently Amended) An electronic apparatus having an electro-optical device comprising, above a substrate:

a data ~~lines~~ line extending in a first direction;

a scanning ~~lines~~ line extending in a second direction and intersecting the data ~~lines;~~ line;

a pixel ~~electrodes~~ electrode and a thin film ~~transistors~~ transistor disposed so as to correspond to an intersection ~~regions~~ region of the data ~~lines~~ line and the scanning ~~lines;~~ line, the thin film transistor including a semiconductor layer;

a storage ~~capacitors~~ capacitor electrically connected to the thin film ~~transistors~~ transistor and the pixel ~~electrodes;~~ electrode;

a relay layer electrically connected with the pixel electrode;

a first contact hole electrically connecting the semiconductor layer of the thin film transistor with the data line;

a second contact hole electrically connecting the semiconductor layer of the thin film transistor with the relay layer; and

a shielding ~~layers~~ layer disposed between the data ~~lines~~ line and the pixel ~~electrodes,~~ electrode,

a nitride ~~films~~ film being included in the shielding ~~layers~~ layer and ~~are~~ being formed along the data ~~lines~~ line and wider than the data ~~lines.~~ line, the shielding layer being formed to cover the first contact hole and the second contact hole as viewed in plan.